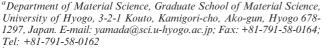
Pressure effect on the electrical conductivity and superconductivity of β -(BDA-TTP)₂I₃

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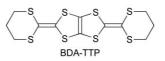
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The pressure-induced electrical conductivity properties of β -(BDA-TTP)₂I₃ have been investigated; the salt exhibits a dramatic change in the conductivity behaviour above *ca*. 10 kbar and undergoes a superconducting transition with an onset near 10 K.

The achievement of organic superconductivity is a major topic in the field of molecular conductors.¹ We have found that the π -electron donor BDA-TTP [2,5-bis(1,3-dithian-2-ylidene)-1,3,4,6-tetrathiapentalene] gives the pressure-induced superconductors β -(BDA- $TTP_{2}MCl_{4}$ (M = Fe and Ga)² as well as the ambient-pressure superconductors β -(BDA-TTP)₂X (X = SbF₆, AsF₆ and PF₆).³ The FeCl₄ and GaCl₄ salts of BDA-TTP at ambient pressure undergo metal-insulator (MI) transitions; however, by applying moderate pressures of less than 4.5 kbar, the MI transitions are suppressed and superconductivity appears in both salts.⁴ Such a large pressure dependence is thought to originate from the conformational flexibility of BDA-TTP. Namely, a flapping motion of the two trimethylene end groups of BDA-TTP with respect to the molecular plane allows the outer dithiane rings to adopt various kinds of chair conformations. For instance, these end groups of BDA-TTP in β- $(BDA-TTP)_2MCl_4$ (M = Fe and Ga) are bonded to the molecular plane from the same side, 2a,5 whereas those in β -(BDA-TTP)₂X(X = SbF_6 , AsF_6 and PF_6) are found with opposite orientation with respect to the molecular plane: the same can be said for BDA-TTP in the neutral state.³ An analogous situation can be encountered in the BEDT-TTF [bis(ethylenedithio)tetrathiafulvalene] conductors, in which, however, two twist conformations, viz., the so-called eclipsed and staggered conformations, are present in the BEDT-TTF donor molecule.^{1a,b} It is therefore expected that compared to the conformational change in BEDT-TTF by a twisting motion of the two ethylene end groups, that in BDA-TTP by a flapping motion leads to further varied physical properties under moderate pressures. This expectation prompted us to investigate the pressure-induced electrical conducting behaviour of other BDA-TTP salts. Herein, we describe what change in the transport properties of (BDA-TTP)₂I₃ is brought about by application of pressure.



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As reported by us earlier,⁶ (BDA-TTP)₂I₃ exhibits semiconducting behaviour with an activation energy of 54 meV. To gain an insight into the derivation of the structure–property relationship, single-crystal X-ray structure determination was undertaken.[†] The salt consists of alternate layers of BDA-TTP donor molecules arranged in the β -packing mode and layers of I₃⁻ anions (Fig. 1a).

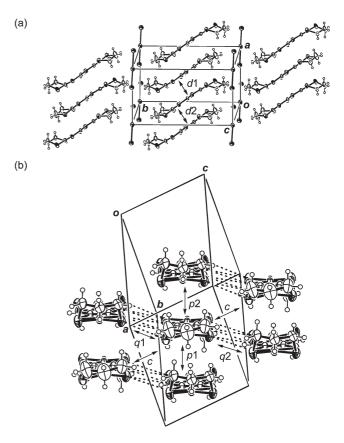


Fig. 1 (a) Crystal structure of β -(BDA-TTP)₂I₃. Interplanar distances *d*l and *d*2 are 3.65 and 3.49 Å, respectively. (b) Donor arrangement in β -(BDA-TTP)₂I₃. Short S···S contacts (<3.70 Å) are shown by broken lines. Intermolecular overlap integrals *p*1, *p*2, *c*, *q*1 and *q*2 (×10⁻³) are 13.7, 5.02, -6.75, 0.20 and -5.28, respectively.

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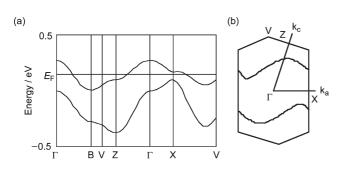


Fig. 2 (a) Band structure and (b) Fermi surface of β -(BDA-TTP)₂I₃.

In the donor layer, the conformation of BDA-TTP, including the orientation of the two trimethylene end groups with respect to the molecular plane, belongs to the same category as found in β - $(BDA-TTP)_2X$ (X = SbF₆, AsF₆ and PF₆). BDA-TTP molecules are dimerized with interplanar distances of 3.65 and 3.49 Å to form a stack along the a-axis. Intermolecular S…S contacts shorter than the van der Waals distance (3.70 Å) occur between donor stacks rather than within a donor stack (Fig. 1b). The overlap integrals between the HOMO's of adjacent donor molecules were calculated on the basis of the extended Hückel method.⁷ A comparison of the intrastack overlap integral ratio of p1 to p2 in β -(BDA-TTP)₂I₃ (2.73) with the corresponding ratios in β -(BDA-TTP)₂MCl₄ (M = Fe, 1.07; M = Ga, 1.10)^{2a,5} indicates a much larger dimerization of donor molecules in β -(BDA-TTP)₂I₃. The tight-binding band calculation led to a one-dimensional (1D) electronic structure and an open Fermi surface along the intrastacking a-direction (Fig. 2), which would be responsible for the semiconducting behaviour.

Fig. 3 shows the magnetic susceptibility of β -(BDA-TTP)₂I₃ as a function of temperature at 0.1 T from 2 to 300 K. The susceptibility is well explained by the 1D antiferromagnetic Heisenberg model, giving a *J* value of -125(3) K and a spin concentration of 46(3)%.⁸ This result implies the possibility of the occurrence of pressure-induced superconductivity in β -(BDA-TTP)₂I₃, because studies of the phase diagrams of TMTSF (tetramethyltetraselenafulvalene)^{9a} and BEDT-TTF^{9b}

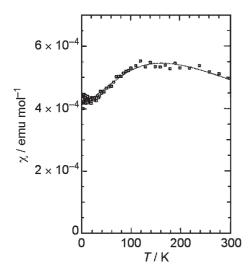


Fig. 3 Temperature dependence of the susceptibility of β -(BDA-TTP)₂I₃. The dotted line represents a theoretical curve for the 1D antiferromagnetic Heisenberg model with J = -125(3) K.

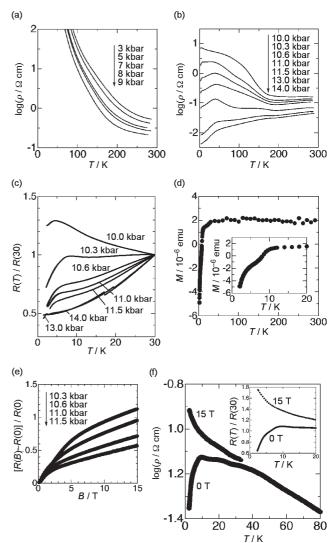


Fig. 4 (a) Temperature dependence of the resistivity of β-(BAD-TTP)₂I₃ at different pressures 3, 5, 7, 8 and 9 kbar from top to bottom. (b) Temperature dependence of the resistivity of β-(BAD-TTP)₂I₃ at different pressures 10.0, 10.3, 10.6, 11.0, 11.5, 13.0 and 14.0 kbar from top to bottom. (c) Temperature dependence of the relative resistance of β-(BAD-TTP)₂I₃ below 30 K under pressures of 10.0 to 14.0 kbar. (d) Temperature dependence of the magnetization for β-(BDA-TTP)₂I₃ under a magnetic field of 0.1 T at 10 kbar. The inset shows the magnetization in the low-temperature region. (e) MR of β-(BDA-TTP)₂I₃ at 1.6 K under different pressures 10.3, 10.6, 11.0 and 11.5 kbar from top to bottom. (f) Magnetic field dependence of the resistance drop in β-(BDA-TTP)₂I₃ at 9.7 kbar. The inset shows the temperature dependence of the relative resistance in the low-temperature region at 0 and 15 T.

superconductors have shown that the superconducting state lies adjacent to the antiferromagnetic insulating state.

We investigated the pressure effect on the electrical transport properties of β -(BDA-TTP)₂I₃ by applying hydrostatic pressures of up to 14 kbar.[‡] The semiconducting behavior observed at ambient pressure remained almost unaltered under pressures of up to 9 kbar (Fig. 4a). Surprisingly, marked changes in the transport behavior took place above 10 kbar (Fig. 4b). At 10.0 kbar, the resistivity showed an almost temperature-independent value from room temperature, a change to semiconducting behavior below *ca*. 190 K and a drop with an onset at 4.5 K. In addition, the onset temperature of the resistance drop reached 8.2 K by means of increasing the pressure by only 0.3 kbar (Fig. 4c); however, with further increases in the pressure, it decreased slowly and no resistance drop was observed at 14.0 kbar. In order to probe whether or not the resistance drop is attributable to a superconducting transition, we examined the Meissner effect of this salt. As shown in Fig. 4d, the salt at 10 kbar exhibited a sudden stepwise decrease in magnetization below 10.5 K under a magnetic field of 0.1 T.[‡] Furthermore, magnetoresistance (MR) measurements at 1.6 K under pressures of 10.3 to 11.5 kbar indicated that the resistance was restored by increasing the magnetic field (Fig. 4e). Also, another sample at 9.7 kbar showed a stepwise resistance drop with an onset at 9.5 K, which completely disappeared by applying a magnetic field of 15 T (Fig. 4f). These results added to the superconductivity of this salt.

In conclusion, we have revealed that β -(BDA-TTP)₂I₃ displays a dramatic divergence between the pressure-induced conducting behavior below 9 kbar and above 10 kbar. It is especially noteworthy that the superconducting transition temperature (T_c) of β -(BDA-TTP)₂I₃ increases with a slight increase in pressure and that the resistive or magnetic $T_{\rm c}$ around 10 kbar can be raised to about 10 K or above. A similar pressure effect on $T_{\rm c}$ prior to reaching its maximum has been found in high-T_c organic superconductors such as ĸ-(BEDT-TTF)2Cu[N(CN)2]Cl,10a its deuterated form κ -(d₈-BEDT-TTF)₂Cu[N(CN)₂]Cl^{10a} and λ - $(BETS)_2GaBr_{1.5}Cl_{2.5}$ [BETS = bis(ethylenedithio)tetraselenafulvalene],^{10b} all of which have T_c 's above 10 K.¹¹ On the other hand, we have failed to detect zero resistance in β -(BDA-TTP)₂I₃ probably due to a small volume fraction in the observed superconducting state. Furthermore, it is very difficult in highpressure experiments to exactly estimate the pressure loss during cooling, so we have been unable to know a pressure value suitable for observing the zero resistance or a sample-independent T_c in β -(BDA-TTP)₂I₃. However, there is a tendency for β -(BDA-TTP)₂I₃ that when the $T_{\rm c}$ is higher, the magnitude of the resistance drop is larger. The realization of a superconducting state with a larger volume fraction and/or a higher T_c may, thus, require fine tuning of the pressure control or application of uniaxial strain. Work currently in progress is addressing this question.

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Notes and references

† Crystal data for (BDA-TTP)₂I₃: C₂₄H₂₄I₃S₁₆, $M_r = 1206.13$, triclinic, space group $P\bar{I}$, a = 9.2460(9) Å, b = 16.792(2) Å, c = 6.4950(7) Å, $\alpha = 95.263(9)^\circ$, $\beta = 106.576(8)^\circ$, $\gamma = 95.766(9)^\circ$, V = 953.9(2) Å³, Z = 1, $\rho_{calcd} = 2.099$ g cm⁻³, $\mu = 3.354$ mm⁻¹, $2\theta_{max} = 55.1^\circ$, $\lambda(Mo_{K\alpha}) = 0.7107$ Å, $\omega - 2\theta$ scan mode, T = 296.2 K, 4780 reflections, of which 4393 were independent and 3231 were included in the refinement [$I > 3.0\sigma(I)$], data collected for Lorentzian and polarization effects; a ϕ -scan absorption correction resulted

in transmission factors ranging from 0.562 to 1.000, solution by direct methods (SIR 92) and refinement on $|F^2|$ by full-matrix least-squares procedures (teXsan for Windows ver. 1.06), 197 parameters, the non-H atoms were refined anisotropically, H atoms were included but not refined, final values R = 0.034, wR = 0.034, GOF = 1.91, maximum positive and negative peaks in ΔF map were 1.59 and -1.26 e Å⁻³, respectively. CCDC 289991. For crystallographic data in CIF or other electronic format see DOI: 10.1039/b516909g

[‡] Variable-temperature conductivity or magnetization measurements under hydrostatic pressure were carried out using a clamped Be–Cu pressure cell with a pressure medium of Daphne 7243 or 7373 oil (Idemitsu Co. Ltd.). Electrical conductivity was measured by the four-probe technique using gold wires attached to the single crystal with carbon paste.

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